Publications and Presentations by Mark Wistey

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Hirsch *h*-index: 29 (Web of Science) or 35 (Google Scholar)

Refereed Publications

1. W. Ha, V. Gambin, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "Long Wavelength GaInNAsSb/GaNAsSb Multiple Quantum Well Lasers," *Electron. Lett.*, Vol. 38, No. 6, pp. 277–8, Mar. 2002.
2. W. Ha, V. Gambin, M. Wistey, S. Bank, S. Kim, J. Harris, "Multiple Quantum Well GaInNAs/GaNAs Ridge-Waveguide Laser Diodes Operating Out to 1.4 μm," *IEEE Photon. Technol. Lett.*, Vol. 14, No. 5, May 2002.
3. V. Gambin, W. Ha, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "GaInNAsSb for 1.3–1.6 μm Long-Wavelength Lasers Grown by Molecular Beam Epitaxy," *J. Select. Topics Quantum Electron.*, Vol. 8, No. 4, pp. 795–800, July 2002.
4. W. Ha, V. Gambin, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "Long Wavelength GaInNAs(Sb) Lasers on GaAs," *J. Quantum Electron.*, Vol. 38, No. 9, pp. 1260–7, Sep. 2002.
5. V. Gambin, V. Lordi, W. Ha, M. Wistey, T. Takizawa, K. Uno, S. Friedrich, J. S. Harris, "Structural changes on annealing of MBE grown (Ga, In) (N, As) as measured by X-ray absorption fine structure," *J. Cryst. Growth*, Vol. 251, No. 1–4, p. 408–411, Apr. 2003.
6. S. Bank, W. Ha, V. Gambin, M. Wistey, H. Yuen, L. Goddard, J. S. Harris, "1.5-μm GaInNAs(Sb) Lasers Grown on GaAs by MBE," *J. Cryst. Growth*, Vol. 251, pp. 367–371, 2003.
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9. M. A. Wistey, S. R. Bank, H. B. Yuen, L. L. Goddard, J. S. Harris, "Monolithic, GaInNAsSb VCSELs at 1460nm on GaAs by MBE," *Electron. Lett.*, 39, pp. 1822–3, Dec. 12, 2003.
10. S. R. Bank, M. A. Wistey, L. L. Goddard, H. B. Yuen, J. S. Harris, "Low Threshold, Continuous Wave, 1.5 μm GaInNAsSb Lasers Grown on GaAs," *IEEE J. Quantum Electron.*, vol. 40, No. 6, pp. 656–664, June 2004.
11. M. A. Wistey, S. R. Bank, H. B. Yuen, L. L. Goddard, J. S. Harris, "GaInNAs(Sb) vertical-cavity surface-emitting lasers at 1.46μm," *J. Vac. Sci. Technol.-B*, 22, No. 3, pp. 1562–1564, May/Jun 2004.
12. T. Gugov, V. Gambin, M. Wistey, H. Yuen, S. Bank, J. S. Harris, "Use of transmission electron microscopy in the characterization of GaInNAs(Sb) quantum well structures grown by molecular beam epitaxy," *J. Vac. Sci. Technol.-B*, 22, No. 3, pp. 1588–1592, May/Jun 2004.
13. J.-X. Fu, S. R. Bank, M. A. Wistey, H. B. Yuen, J. S. Harris, "Solid-source molecular-beam epitaxy growth of GaInNAsSb/InGaAs single quantum well on InP with photoluminescence peak wavelength at 2.04 μm," *J. Vac. Sci. Technol.-B*, 22, No. 3, pp. 1463–1467, May/Jun 2004.
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